

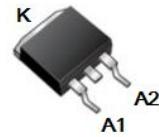
WSB5552TH

Power Schottky Barrier Rectifier

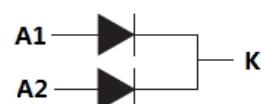
[Http://www.sh-willsemi.com](http://www.sh-willsemi.com)

Features

- 2x5A average rectified forward current
- Low forward voltage and Low leakage current
- Excellent high junction temperature stability
- High forward surge capability



TO-263E-2L



Circuit



Marking

Applications

- High frequency switch model power supplies
- DC-DC Convertors, Power adapters

Absolute maximum ratings				
Parameter	Symbol	Value	Unit	
Reverse voltage (repetitive peak)	V_{RM}	100	V	
Reverse voltage (DC)	V_R	100	V	
Average rectified forward current	Per diode	I_F	5	A
	Per device	I_F	10	A
Peak Forward Surge Current ⁽¹⁾	I_{FSM}	100	A	
Junction temperature	T_J	150	$^{\circ}\text{C}$	
Operating temperature	T_{opr}	-55 ~ 150	$^{\circ}\text{C}$	
Storage temperature	T_{stg}	-55 ~ 150	$^{\circ}\text{C}$	
Thermal Resistance Ratings				
Maximum Thermal Resistance Junction To case (Per leg)	$R_{\theta JC}$	2.2	$^{\circ}\text{C/W}$	

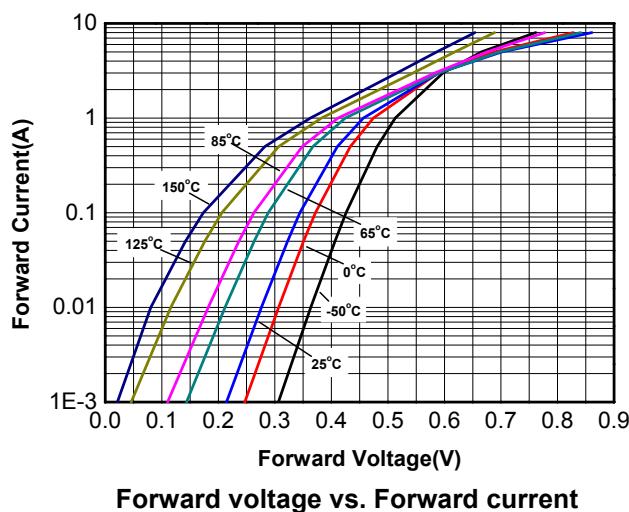
Order information			
Device	Package	Marking	Shipping
WSB5552TH-3/T	TO-263E-2L	WSB5552THYW ⁽²⁾	800/Reel&Tape

Note 1: Pulse Width=8.3ms, Single Half Sine Pulse

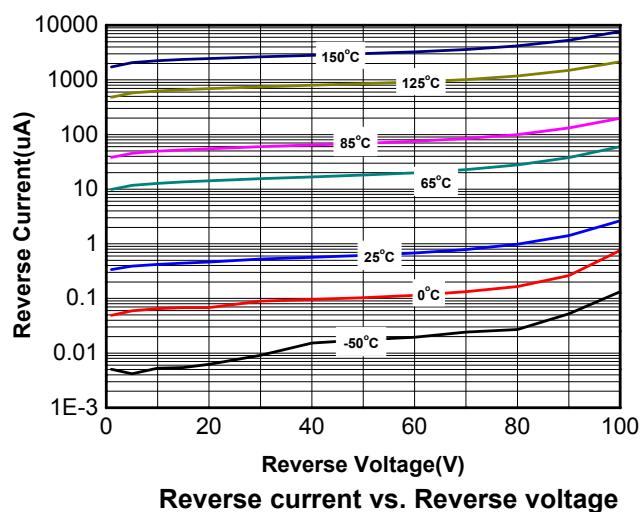
Note 2: WSB5552= Device code; TH=Special Code; Y=Year; W=Week (A~z)

Electronics characteristics ($T_A=25^\circ\text{C}$, Per diode)						
Parameter	Symbol	Condition	Min.	Typ.	Max.	Unit
Reverse Breakdown Voltage	V_R	$I_R=0.5\text{mA}$	100	-	-	V
Forward voltage	V_F	$I_F=5\text{A}$	-	-	0.80	V
Reverse current	I_R	$V_R=100\text{V}$	-	-	0.1	mA
Junction capacitance	C_J	$V_R=25\text{V}, F=1\text{MHz}$	-	62	-	pF

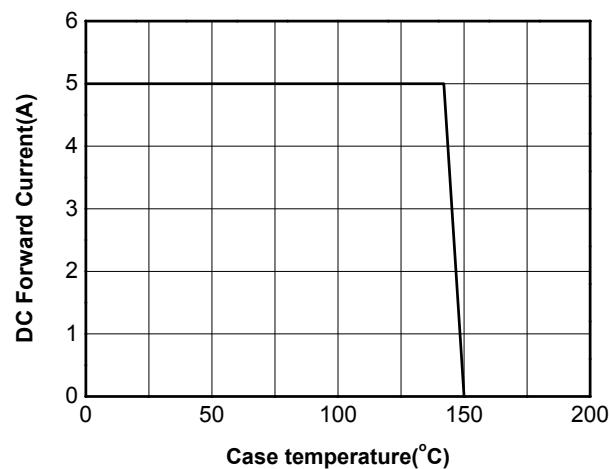
Typical characteristics ($T_a=25^\circ\text{C}$, Per diode)



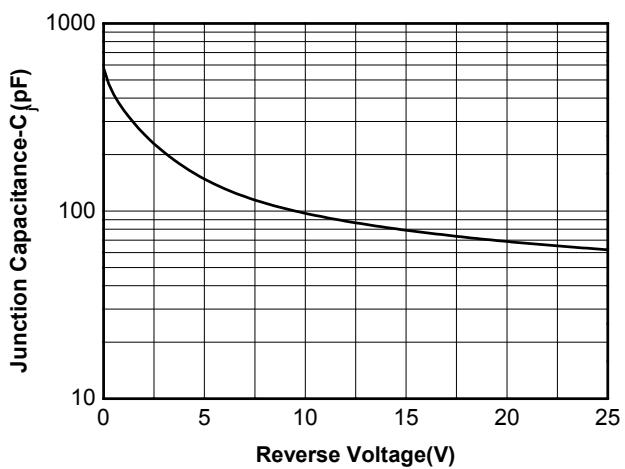
Forward voltage vs. Forward current



Reverse current vs. Reverse voltage



Forward Current Derating Curve



Junction capacitance vs. Reverse voltage

TO-263E-2L
